General Purpose Transistors

PNP Silicon

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|--|------------------|-------------------|------|
| Collector-Emitter Voltage BC856, SBC856 BC857, SBC857 BC858, NSVBC858, BC859 | V _{CEO} | -65 -45 -30 | > |
| Collector-Base Voltage BC856, SBC856 BC857, SBC857 BC858, NSVBC858, BC859 | V _{СВО} | -80 -50 -30 | V |
| Emitter-Base Voltage | V _{EBO} | -5.0 | V |
| Collector Current – Continuous | I _C | -100 | mAdc |
| Collector Current – Peak | Ic | -200 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------------------------|-------------|-------------|
| Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C | P _D | 225 1.8 | mW mW/°C |
| Thermal Resistance, Junction–to–Ambient | $R_{\theta JA}$ | 556 | °C/W |
| Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C | P _D | 300 2.4 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 417 | °C/W |
| Junction and Storage Temperature | T _J , T _{stg} | -55 to +150 | °C |

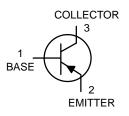
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



xx = Device Code

xx = (Refer to page 6)

M = Date Code*

= Pb–Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

1

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|--|----------------------|----------------------|--------------|----------------|----------|
| OFF CHARACTERISTICS | | | | | |
| Collector – Emitter Breakdown Voltage BC856, SBC856 Series (I _C = -10 mA) BC857, SBC857 Series BC858, NSBVC858 BC859 Series | V _{(BR)CEO} | -65 -45 -30 | - - - | - - - | V |
| $ \begin{array}{lll} & \text{Collector-Emitter Breakdown Voltage} & \text{BC856 S, SBC856eries} \\ & \text{(I}_{\text{C}} = -10~\mu\text{A},~\text{V}_{\text{EB}} = 0) & \text{BC857A, SBC857A, BC857B, SBC857B Only} \\ & & \text{BC858, NSVB858, BC859 Series} \end{array} $ | V _{(BR)CES} | -80 -50 -30 | - - - | - - - | V |
| Collector – Base Breakdown Voltage BC856, SBC856 Series $(I_C = -10~\mu\text{A})$ BC857, SBC857 Series BC858, NSVBC858, BC859 Series | V _{(BR)CBO} | -80 -50 -30 | - - - | - - - | V |
| Emitter – Base Breakdown Voltage BC856, SBC856 Series $(I_E = -1.0 \ \mu\text{A})$ BC857, SBC857 Series BC858, NSVBC858, BC859 Series | V _{(BR)EBO} | -5.0 -5.0 -5.0 | - - - | - - - | V |
| Collector Cutoff Current ($V_{CB} = -30 \text{ V}$) ($V_{CB} = -30 \text{ V}$, $T_A = 150^{\circ}\text{C}$) | I _{CBO} | - - | _ _ | –15 –4.0 | nA μA |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain BC856A, SBC856A, BC857A, SBC857A, BC858A $(I_C = -10 \mu A, V_{CE} = -5.0 \text{ V})$ BC856B, SBC856B, BC857B, SBC858B, NSVBC858B | h _{FE} | | 90 150 | _ _ | - |
| BC857C, SBC857C BC858C | | _ | 270 | - | |
| $(I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V})$ BC856A, SBC856A, BC857A, SBC857A, BC858A | | 125 | 180 | 250 | |
| BC856B, SBC856B, BC857B, SBC857B, BC858B, NSVBC858B, BC859B BC857C, SBC857C, BC858C, BC859C | | 220 420 | 290 520 | 475 800 | |
| Collector – Emitter Saturation Voltage ($I_C = -10$ mA, $I_B = -0.5$ mA) ($I_C = -100$ mA, $I_B = -5.0$ mA) | V _{CE(sat)} | - - | _ _ | -0.3 -0.65 | V |
| Base – Emitter Saturation Voltage (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA) | V _{BE(sat)} | - - | -0.7 -0.9 | - - | V |
| Base – Emitter On Voltage ($I_C = -2.0$ mA, $V_{CE} = -5.0$ V) ($I_C = -10$ mA, $V_{CE} = -5.0$ V) | V _{BE(on)} | -0.6 - | - - | -0.75 -0.82 | V |
| SMALL-SIGNAL CHARACTERISTICS | | | | | |
| Current – Gain – Bandwidth Product $(I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz})$ | f _T | 100 | _ | _ | MHz |
| Output Capacitance (V _{CB} = -10 V, f = 1.0 MHz) | C _{ob} | _ | _ | 4.5 | pF |
| Noise Figure (I _C = -0.2 mA, V _{CE} = -5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz) BC856, SBC856, BC857, SBC857, BC858, NSVBC858 Series BC859 Series | NF | - - | - - | 10 4.0 | dB |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BC857/BC858/BC859/SBC857/NSVBC858

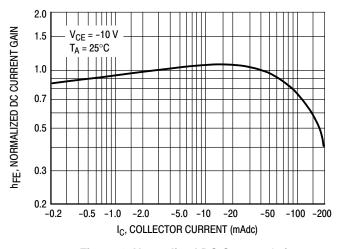


Figure 1. Normalized DC Current Gain

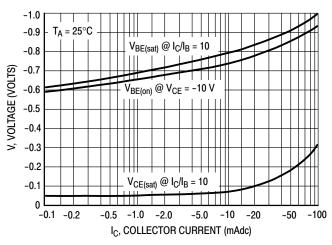


Figure 2. "Saturation" and "On" Voltages

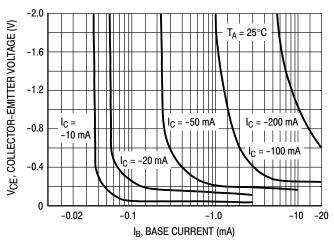


Figure 3. Collector Saturation Region

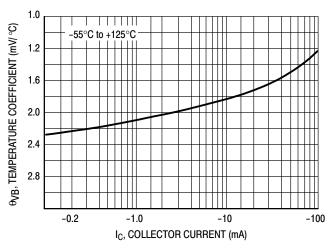


Figure 4. Base-Emitter Temperature Coefficient

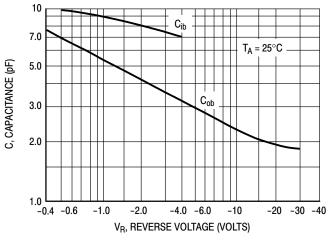


Figure 5. Capacitances

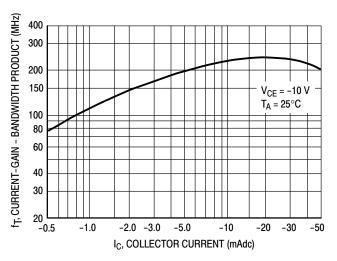


Figure 6. Current-Gain - Bandwidth Product

BC856/SBC856

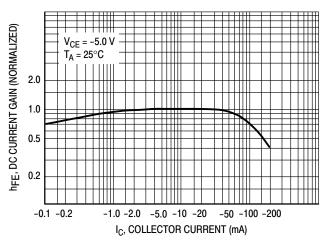


Figure 7. DC Current Gain

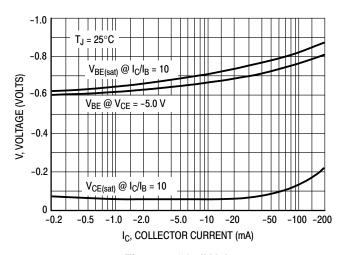


Figure 8. "On" Voltage

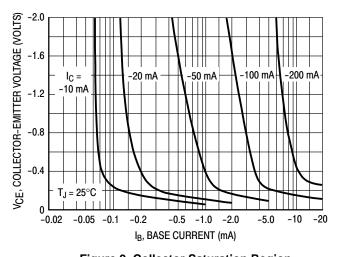


Figure 9. Collector Saturation Region

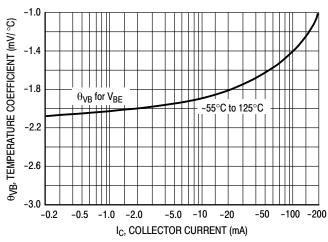


Figure 10. Base-Emitter Temperature Coefficient

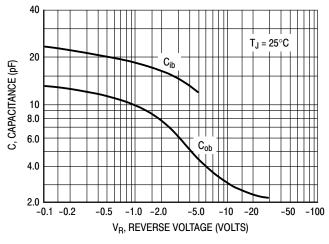


Figure 11. Capacitance

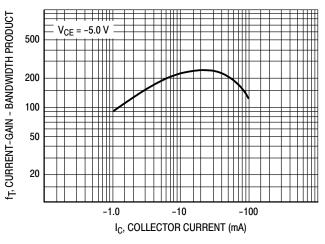


Figure 12. Current-Gain - Bandwidth Product

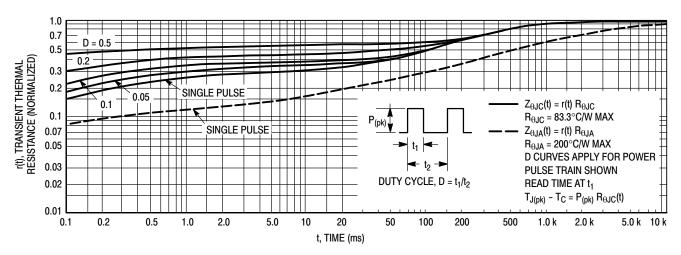


Figure 13. Thermal Response

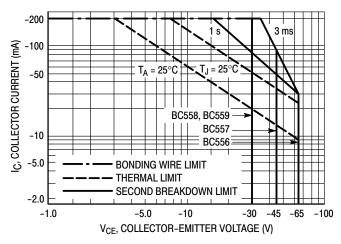


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^{\circ}C$; T_{C} or T_{A} is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

ORDERING INFORMATION

| Device | Marking | Package | Shipping [†] | |
|----------------|---------|---------------------|-----------------------|--|
| BC856ALT1G | 3A | SOT-23 | 3,000 / Tape & Reel | |
| SBC856ALT1G* | | (Pb-Free) | | |
| BC856ALT3G | | | 10,000 / Tape & Reel | |
| BC856BLT1G | 3B | SOT-23 | 3,000 / Tape & Reel | |
| SBC856BLT1G* | | (Pb-Free) | | |
| BC856BLT3G | | | 10,000 / Tape & Reel | |
| SBC856BLT3G* | | | | |
| BC857ALT1G | 3E | SOT-23 | 3,000 / Tape & Reel | |
| SBC857ALT1G* | | (Pb-Free) | | |
| BC857BLT1G | 3F | SOT-23 | 3,000 / Tape & Reel | |
| SBC857BLT1G* | | (Pb-Free) | | |
| BC857BLT3G | | | 10,000 / Tape & Reel | |
| NSVBC857BLT3G* | | | | |
| BC857CLT1G | 3G | | 3,000 / Tape & Reel | |
| SBC857CLT1G* | | (Pb-Free) | | |
| BC857CLT3G | | | 10,000 / Tape & Reel | |
| BC858ALT1G | 3J | SOT-23 (Pb-Free) | 3,000 / Tape & Reel | |
| BC858BLT1G | 3K | SOT-23 | | |
| NSVBC858BLT1G* | | (Pb-Free) | | |
| BC858BLT3G | 3L | SOT-23 (Pb-Free) | 10,000 / Tape & Reel | |
| BC858CLT1G | | SOT-23 (Pb-Free) | 3,000 / Tape & Reel | |
| BC858CLT3G | | SOT-23 (Pb-Free) | 10,000 / Tape & Reel | |
| BC859BLT1G | 4B | SOT-23 (Pb-Free) | 3,000 / Tape & Reel | |
| BC859BLT3G | | SOT-23 (Pb-Free) | 10,000 / Tape & Reel | |
| BC859CLT1G | 4C | SOT-23 (Pb-Free) | 3,000 / Tape & Reel | |
| BC859CLT3G | | SOT-23 (Pb-Free) | 10,000 / Tape & Reel | |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

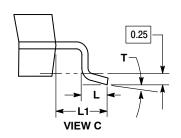


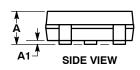
SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

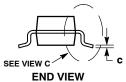
DATE 30 JAN 2018

SCALE 4:1 D Ε - 3X b

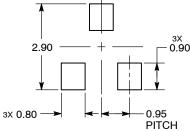
TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

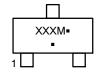
3. ANODE

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| | MILLIMETERS | | | | INCHES | |
|-----|-------------|------|------|-------|--------|-------|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| Α | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| С | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| е | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| Т | O٥ | | 10° | n۰ | | 10° |

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

| STYLE 1 THRU 5: CANCELLED | STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE | | |
|--|---|---|---|---|---|
| STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE | STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE | STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE | STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE |
| STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE | STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE | STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE | STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE | STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE | STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE |
| STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN | STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT | STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE | STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE | STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION |
| STYLE 27: PIN 1. CATHODE 2. CATHODE | STYLE 28: PIN 1. ANODE 2. ANODE | | | | |

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|------------------|-----------------|---|-------------|
| DESCRIPTION: | SOT-23 (TO-236) | | PAGE 1 OF 1 |

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